

Silicon NPN Power Transistors

2SC3569

DESCRIPTION

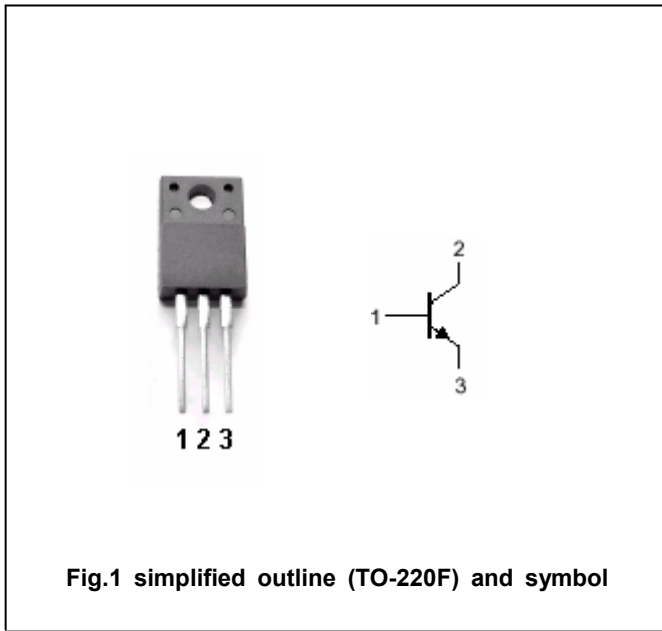
- With TO-220F package
- Low collector saturation voltage

APPLICATIONS

- High speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		2	A
I _{CM}	Collector current-peak		4	A
I _B	Base current		1	A
P _C	Collector power dissipation	T _C =25°C	15	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.5A; I _B =0.1A; L=1mH	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.5 A; I _B =0.1A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =0.5 A; I _B =0.1A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =400V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =5V	20		80	
h _{FE-2}	DC current gain	I _C =0.5A ; V _{CE} =5V	10			

Switching times

t _{on}	Turn-on time	I _C =0.5A; R _L =300Ω I _{B1} =- I _{B2} =0.1A V _{CC} =150V			1.0	μs
t _s	Storage time				2.5	μs
t _f	Fall time				1.0	μs

◆ h_{FE-1} classifications

R	O	Y
20-40	30-60	40-80

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PACKAGE OUTLINE

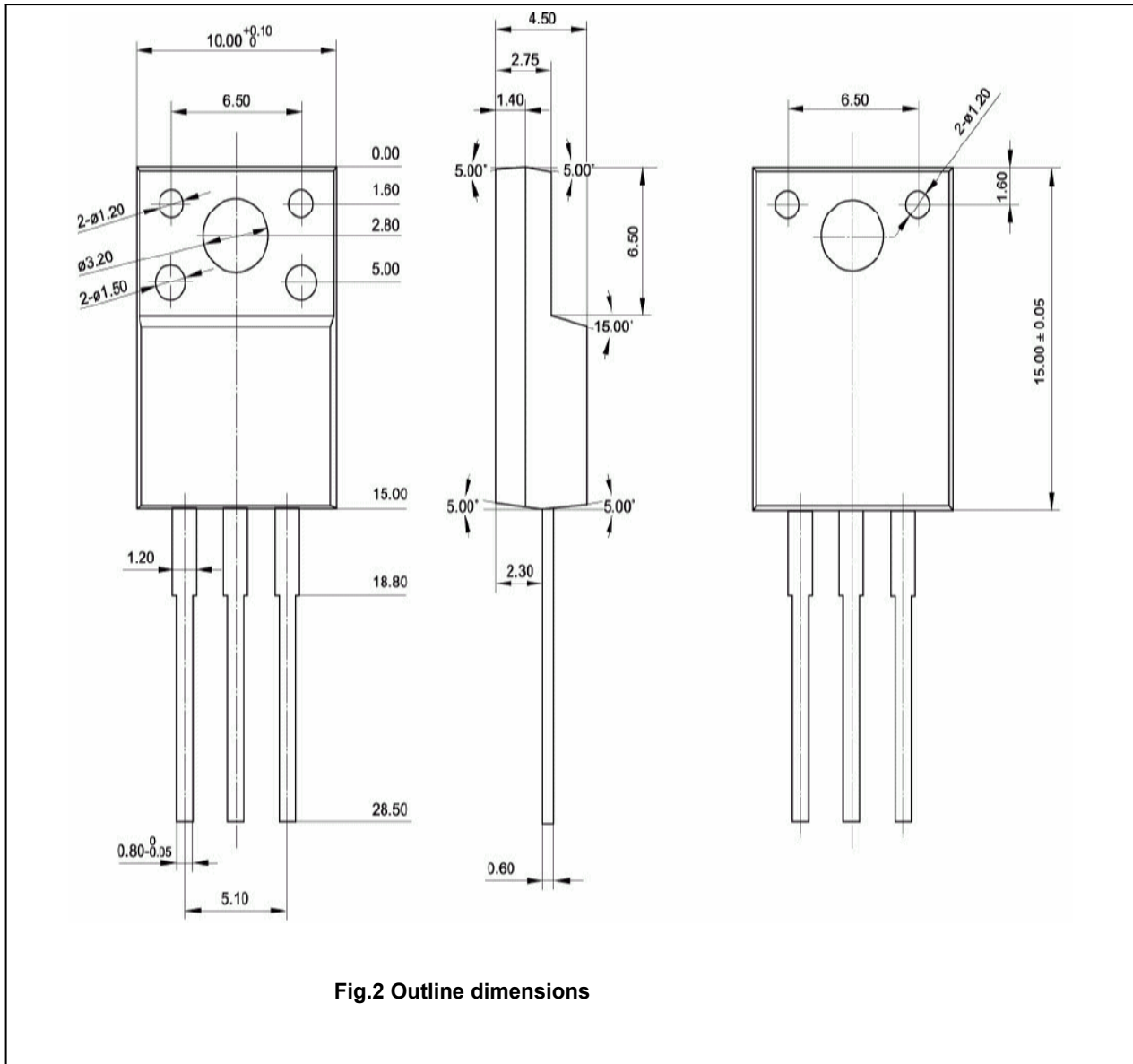


Fig.2 Outline dimensions